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IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Application Serial No. 09/879,335
Filing Date June 11, 2001
Inventor Vishnu K. Agarwal, et al
Assignee Micron Technology, Inc.
Group Art Unit 2813
Examiner Y. Huynh
Attorney's Docket No. MI22-1568
Title: Capacitor Forming Methods with Barrier Layers to Threshold Voltage Shift
Inducing Material

PRELIMINARY AMENDMENT TO ACCOMPANY RCE FILING

To: Box RCE
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AMENDMENTS

In the Claims

Please add new claims 58-65 in accordance with 37 C.F.R. 1.121(c)(1)(i).

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58. The method of claim 1 wherein the barrier layer is formed on the insulation layer.
59. The method of claim 1 further comprising providing V_t shift inducing material over the insulation layer.
60. The method of claim 16 wherein the barrier layer is formed on the insulation layer.
61. The method of claim 22 wherein the barrier layer is formed on the substrate.